

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,949,402 B2
DATED : September 27, 2005
INVENTOR(S) : John T. Moore et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], **References Cited**, FOREIGN PATENT DOCUMENTS,

"JP 56126915 A 10/1981" should read -- JP 56126916 A 10/1981 --.

OTHER PUBLICATIONS,

"Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64." should read

-- Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64. --;

"Deamaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191" should read

-- Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191. --;

"El Ghrandi. R.; Calas, J.; Gailbert., G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273." should read

-- El Ghrandi. R.; Calas, J.; Galibert., G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273. --;

"Halfz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Apply. Phys. 54 (1983) 1950-1954." should read

-- Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses. J. Appl. Phys. 54 (1983) 1950-1954. --;

"Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258." should read

-- Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258. --;

"Lolobov, A.V., "Photodoping of amorphous chalcogenides by metals", Advance in Physics, 1991, vol. 40, No. 5, pp. 625-684." should read

-- Kolobov, A.V., "Photodoping of amorphous chalcogenides by metals", Advance in Physics, 1991, vol. 40, No. 5, pp. 625-684. --; and

"Huggett et al., *Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF*, 42 Appl. Phys. Lett., No. 7, pp. 592-594 (Apr. 1983)."

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Title page (cont'd),
should read

-- Huggett et al., *Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆*, 42 Appl. Phys. Lett., No. 7, pp. 592-594 (Apr. 1983). --.

Column 3,

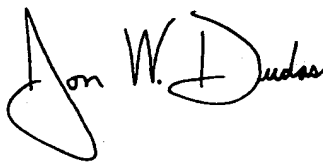
Line 30, reads "example such" and should read -- example of such --.

Column 7,

Line 44, reads "portion of said of said" and should read -- portion of said --.

Signed and Sealed this

Twenty-first Day of February, 2006

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looping initial "J" and a distinct "D".

JON W. DUDAS

Director of the United States Patent and Trademark Office